

Amendments to the Specification

Please replace the title as follows:

FERROELECTRIC MEMORY DEVICE, ~~METHOD OF MANUFACTURING THE SAME,~~
~~AND EMBEDDED DEVICE~~

Please add the following paragraph between the title and the first line of text as follows:

now Patent No. 6,727,536
This is a Division of Application No. 09/934,550 filed August 23, 2001. The entire disclosure of the prior application is hereby incorporated by reference herein in its entirety.

Please replace the paragraph beginning on page 2, line 25, with the following rewritten paragraph:

(1) The ferroelectric layer may be disposed linearly along the first signal electrodes. Specifically, the ferroelectric layer may be selectively disposed over the first signal electrodes. In this case, since the ferroelectric layer is formed linearly along the first signal electrodes, the parasitic capacitance or load capacitance of the second signal electrodes can be decreased.

Please replace the paragraph beginning on page 3, line 22, with the following rewritten paragraph:

(2) The ferroelectric layer may be disposed linearly along the second signal electrodes. Specifically, the ferroelectric layer may be selectively disposed under the second signal electrodes. In this case, since the ferroelectric layer is formed linearly along the second signal electrodes, the parasitic capacitance or load capacitance of the first signal electrodes can be decreased.